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Kind regards,

Team Nexperia



2PD601ART

50 V, 100 mA NPN general-purpose transistor Rev. 01 — 15 March 2007

Product data sheet

Product profile

1.1 General description

NPN general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: 2PB709ART.

1.2 Features

- General-purpose transistor
- Small SMD plastic package

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V};$ $I_C = 2 \text{ mA}$	210	-	340	

2. Pinning information

Table 2. **Pinning**

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter	3	3
3	collector	1 2	1 —
			sym021



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3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
2PD601ART	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
2PD601ART	C3*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

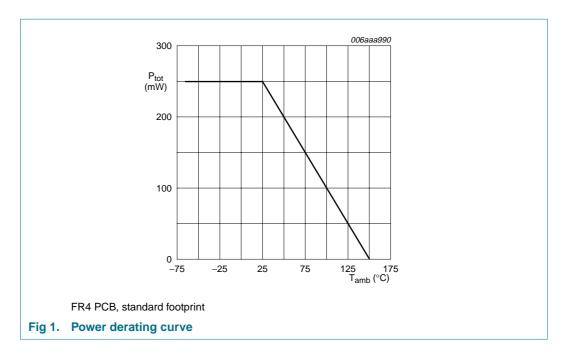
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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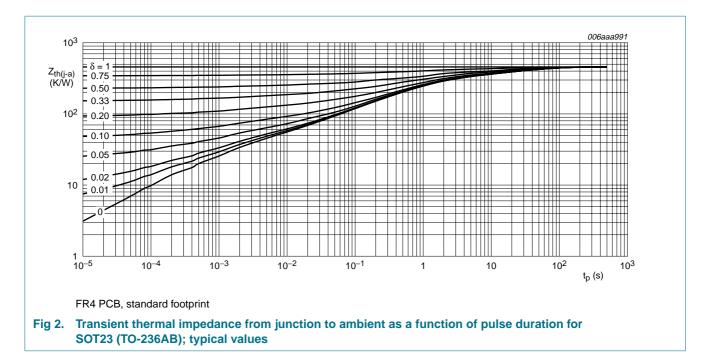
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	140	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

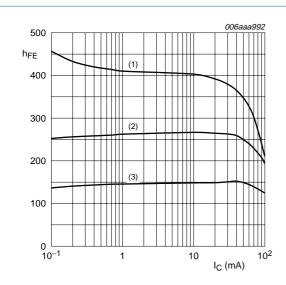
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}$	-	-	10	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	10	nA
h _{FE}	DC current gain	$V_{CE} = 2 V;$ $I_{C} = 100 \text{ mA}$	90	-	-	
		$V_{CE} = 10 \text{ V};$ $I_{C} = 2 \text{ mA}$	210	-	340	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA};$ $I_B = 10 \text{ mA}$	<u>[1]</u> -	-	250	mV
f _T	transition frequency	$V_{CE} = 10 \text{ V};$ $I_{C} = 2 \text{ mA};$ $f = 100 \text{ MHz}$	100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	3	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

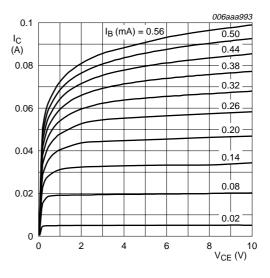
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$$V_{CE} = 10 \text{ V}$$

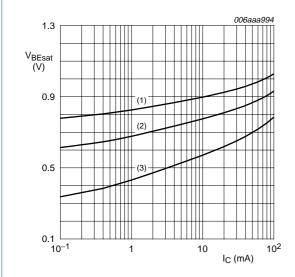
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

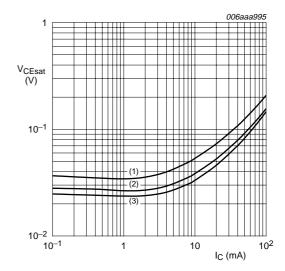
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) T_{amb} = 25 °C
- (3) T_{amb} = 150 °C

Fig 5. Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$

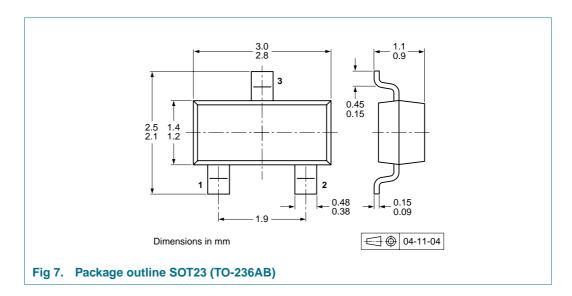
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(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

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8. Package outline



9. Packing information

Table 8. Packing methods

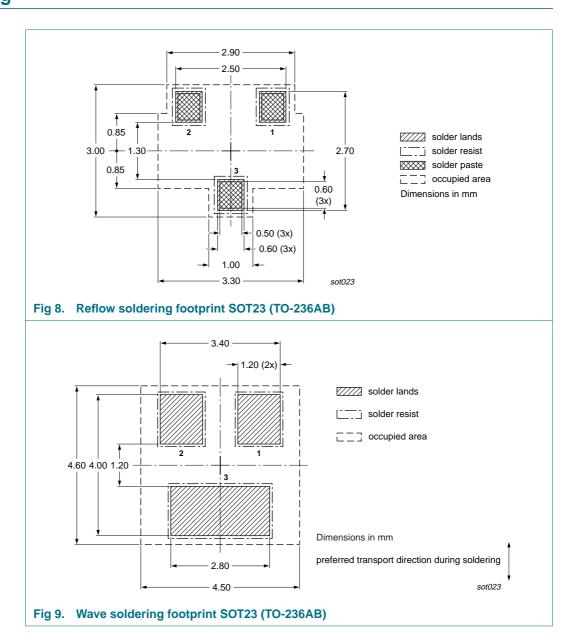
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing quantity		quantity
			3000	10000
2PD601ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 13.

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2PD601ART_1	20070315	Product data sheet	-	-

50 V, 100 mA NPN general-purpose transistor

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

2PD601ART

50 V, 100 mA NPN general-purpose transistor

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